

**FEATURES**

**Low Insertion Loss and On Resistance: 2.2  $\Omega$  Typical**

**On Resistance Flatness 0.5  $\Omega$  Typical**

**Automotive Temperature Range**

**-40°C to +125°C**

**-3 dB Bandwidth = 240 MHz**

**Single 3 V/5 V Supply Operation**

**Rail-to-Rail Operation**

**Very Low Distortion: 0.5%**

**Low Quiescent Supply Current (1 nA Typical)**

**Fast Switching Times**

**$t_{ON}$  7 ns**

**$t_{OFF}$  4 ns**

**TTL/CMOS Compatible**

**APPLICATIONS**

**USB 1.1 Signal Switching Circuits**

**Cell Phones**

**PDAs**

**Battery-Powered Systems**

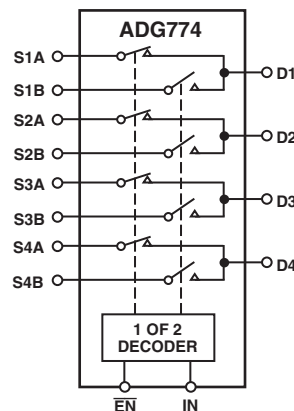
**Communications Systems**

**Data Acquisition Systems**

**Token Ring 4 Mbps/16 Mbps**

**Audio and Video Switching**

**Relay Replacement**

**FUNCTIONAL BLOCK DIAGRAM**

**GENERAL DESCRIPTION**

The ADG774 is a monolithic CMOS device comprising four 2:1 multiplexer/demultiplexers with high impedance outputs. The CMOS process provides low power dissipation yet gives high switching speed and low on resistance. The on resistance variation is typically less than 0.5  $\Omega$  with an input signal ranging from 0 V to 5 V.

The bandwidth of the ADG774 is greater than 200 MHz; this, coupled with low distortion (typically 0.5%), makes the part suitable for switching USB 1.1 data signals and fast Ethernet signals.

The on resistance profile is very flat over the full analog input range ensuring excellent linearity and low distortion when switching audio signals. Fast switching speed, coupled with high signal bandwidth, also makes the parts suitable for video signal switching. CMOS construction ensures ultralow power dissipation, making the parts ideally suited for portable and battery-powered instruments.

The ADG774 operates from a single 3.3 V/5 V supply and is TTL logic compatible. The control logic for each switch is shown in the Truth Table.

These switches conduct equally well in both directions when ON, and have an input signal range that extends to the supplies. In the OFF condition, signal levels up to the supplies are blocked. The ADG774 switches exhibit break-before-make switching action.

**PRODUCT HIGHLIGHTS**

1. Wide -3 dB Bandwidth, 240 MHz.
2. Ultralow Power Dissipation.
3. Extended Signal Range.  
The ADG774 is fabricated on a CMOS process giving an increased signal range that fully extends to the supply rails.
4. Low Leakage Over Temperature.
5. Break-Before-Make Switching.  
This prevents channel shorting when the switches are configured as a multiplexer.
6. Crosstalk Typically -70 dB @ 30 MHz.
7. Off Isolation Typically -60 dB @ 10 MHz.

**REV. C**

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# ADG774—SPECIFICATIONS

**SINGLE SUPPLY** ( $V_{DD} = 5\text{ V} \pm 10\%$ ,  $GND = 0\text{ V}$ . All specifications  $T_{MIN}$  to  $T_{MAX}$  unless otherwise noted.)

| Parameter                                                | B Version <sup>1</sup> |                |                        | Unit    | Test Conditions/Comments                                                                                   |
|----------------------------------------------------------|------------------------|----------------|------------------------|---------|------------------------------------------------------------------------------------------------------------|
|                                                          | +25°C                  | –40°C to +85°C | –40°C to +125°C        |         |                                                                                                            |
| ANALOG SWITCH                                            |                        |                |                        |         |                                                                                                            |
| Analog Signal Range                                      |                        |                | 0 V to V <sub>DD</sub> | V       | V <sub>D</sub> = 0 V to V <sub>DD</sub> , I <sub>S</sub> = –10 mA                                          |
| On Resistance (R <sub>ON</sub> )                         | 2.2                    |                |                        | Ω typ   |                                                                                                            |
|                                                          |                        | 5              | 7                      | Ω max   |                                                                                                            |
| On Resistance Match between Channels (ΔR <sub>ON</sub> ) | 0.15                   |                |                        | Ω typ   | V <sub>D</sub> = 0 V to V <sub>DD</sub> , I <sub>S</sub> = –10 mA                                          |
|                                                          |                        | 0.5            | 0.5                    | Ω max   |                                                                                                            |
| On Resistance Flatness (R <sub>FLAT(ON)</sub> )          | 0.5                    |                |                        | Ω typ   | V <sub>D</sub> = 0 V to V <sub>DD</sub> , I <sub>S</sub> = –1 mA                                           |
|                                                          |                        | 1              | 1                      | Ω max   |                                                                                                            |
| LEAKAGE CURRENTS                                         |                        |                |                        |         |                                                                                                            |
| Source OFF Leakage I <sub>S</sub> (OFF)                  | ±0.01                  |                |                        | nA typ  | V <sub>D</sub> = 4.5 V, V <sub>S</sub> = 1 V; V <sub>D</sub> = 1 V, V <sub>S</sub> = 4.5 V; Test Circuit 2 |
|                                                          | ±0.5                   | ±1             | ±1.5                   | nA max  |                                                                                                            |
| Drain OFF Leakage I <sub>D</sub> (OFF)                   | ±0.01                  |                |                        | nA typ  | V <sub>D</sub> = 4.5 V, V <sub>S</sub> = 1 V; V <sub>D</sub> = 1 V, V <sub>S</sub> = 4.5 V; Test Circuit 2 |
|                                                          | ±0.5                   | ±1             | ±1.5                   | nA max  |                                                                                                            |
| Channel ON Leakage I <sub>D</sub> , I <sub>S</sub> (ON)  | ±0.01                  |                |                        | nA typ  | V <sub>D</sub> = V <sub>S</sub> = 4.5 V; V <sub>D</sub> = V <sub>S</sub> = 1 V; Test Circuit 3             |
|                                                          | ±0.5                   | ±1             | ±1.5                   | nA max  |                                                                                                            |
| DIGITAL INPUTS                                           |                        |                |                        |         |                                                                                                            |
| Input High Voltage, V <sub>INH</sub>                     |                        |                | 2.0                    | V min   | V <sub>IN</sub> = V <sub>INL</sub> or V <sub>INH</sub>                                                     |
| Input Low Voltage, V <sub>INL</sub>                      |                        |                | 0.8                    | V max   |                                                                                                            |
| Input Current                                            |                        |                |                        |         |                                                                                                            |
| I <sub>INL</sub> or I <sub>INH</sub>                     | 0.001                  |                |                        | μA typ  |                                                                                                            |
|                                                          |                        |                | ±0.5                   | μA max  |                                                                                                            |
| DYNAMIC CHARACTERISTICS <sup>2</sup>                     |                        |                |                        |         |                                                                                                            |
| t <sub>ON</sub>                                          |                        | 7              |                        | ns typ  | R <sub>L</sub> = 100 Ω, C <sub>L</sub> = 35 pF, V <sub>S</sub> = +3 V; Test Circuit 4                      |
|                                                          |                        | 15             | 20                     | ns max  |                                                                                                            |
| t <sub>OFF</sub>                                         |                        | 4              |                        | ns typ  | R <sub>L</sub> = 100 Ω, C <sub>L</sub> = 35 pF, V <sub>S</sub> = +3 V; Test Circuit 4                      |
|                                                          |                        | 8              | 9                      | ns max  |                                                                                                            |
| Break-Before-Make Time Delay, t <sub>D</sub>             |                        | 5              |                        | ns typ  | R <sub>L</sub> = 100 Ω, C <sub>L</sub> = 35 pF, V <sub>S1</sub> = V <sub>S2</sub> = +5 V; Test Circuit 5   |
|                                                          |                        | 1              |                        | ns min  |                                                                                                            |
| Off Isolation                                            |                        | –65            |                        | dB typ  | R <sub>L</sub> = 100 Ω, f = 10 MHz; Test Circuit 7                                                         |
| Channel-to-Channel Crosstalk                             |                        | –75            |                        | dB typ  |                                                                                                            |
| Bandwidth –3 dB                                          |                        | 240            |                        | MHz typ | R <sub>L</sub> = 100 Ω; Test Circuit 6                                                                     |
| Distortion                                               |                        | 0.5            |                        | % typ   | R <sub>L</sub> = 100 Ω                                                                                     |
| Charge Injection                                         |                        | 10             |                        | pC typ  | C <sub>L</sub> = 1 nF; Test Circuit 9                                                                      |
| C <sub>S</sub> (OFF)                                     |                        | 10             |                        | pF typ  | f = 1 kHz                                                                                                  |
| C <sub>D</sub> (OFF)                                     |                        | 20             |                        | pF typ  | f = 1 kHz                                                                                                  |
| C <sub>D</sub> , C <sub>S</sub> (ON)                     |                        | 30             |                        | pF typ  | f = 1 MHz                                                                                                  |
| POWER REQUIREMENTS                                       |                        |                |                        |         |                                                                                                            |
| I <sub>DD</sub>                                          |                        | 1              | 1                      | μA max  | V <sub>DD</sub> = +5.5 V<br>Digital Inputs = 0 V or V <sub>DD</sub>                                        |
|                                                          | 0.001                  |                |                        | μA typ  |                                                                                                            |
| I <sub>IN</sub>                                          |                        | 1              | 1                      | μA typ  | V <sub>IN</sub> = +5 V<br>V <sub>S</sub> /V <sub>D</sub> = 0 V                                             |
| I <sub>O</sub>                                           |                        | 100            |                        | mA max  |                                                                                                            |

## NOTES

<sup>1</sup>Temperature range: B Version, –40°C to +125°C.

<sup>2</sup>Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

# SINGLE SUPPLY (V<sub>DD</sub> = 3 V ± 10%, GND = 0 V. All specifications T<sub>MIN</sub> to T<sub>MAX</sub> unless otherwise noted.)

| Parameter                                                | B Version <sup>1</sup> |         |                        | Unit             | Test Conditions/Comments                                                                                   |
|----------------------------------------------------------|------------------------|---------|------------------------|------------------|------------------------------------------------------------------------------------------------------------|
|                                                          | +25°C                  | +85°C   | +125°C                 |                  |                                                                                                            |
| ANALOG SWITCH                                            |                        |         |                        |                  |                                                                                                            |
| Analog Signal Range                                      | 4                      |         | 0 V to V <sub>DD</sub> | V                | V <sub>D</sub> = 0 V to V <sub>DD</sub> , I <sub>S</sub> = –10 mA                                          |
| On Resistance (R <sub>ON</sub> )                         |                        |         |                        | Ω typ<br>Ω max   |                                                                                                            |
|                                                          |                        | 8       | 9                      |                  |                                                                                                            |
| On Resistance Match between Channels (ΔR <sub>ON</sub> ) | 0.15                   |         |                        | Ω typ<br>Ω max   | V <sub>D</sub> = 0 V to V <sub>DD</sub> , I <sub>S</sub> = –10 mA                                          |
|                                                          |                        | 0.5     | 0.5                    |                  |                                                                                                            |
| On Resistance Flatness (R <sub>FLAT(ON)</sub> )          | 2                      |         |                        | Ω typ<br>Ω max   | V <sub>D</sub> = 0 V to V <sub>DD</sub> , I <sub>S</sub> = –10 mA                                          |
|                                                          |                        | 4       | 4                      |                  |                                                                                                            |
| LEAKAGE CURRENTS                                         |                        |         |                        |                  |                                                                                                            |
| Source OFF Leakage I <sub>S</sub> (OFF)                  | ±0.01<br>±0.5          | ±1      | ±1.5                   | nA typ<br>nA max | V <sub>D</sub> = 3 V, V <sub>S</sub> = 1 V; V <sub>D</sub> = 1 V, V <sub>S</sub> = 3 V;<br>Test Circuit 2  |
| Drain OFF Leakage I <sub>D</sub> (OFF)                   | ±0.01<br>±0.5          |         |                        | nA typ<br>nA max | V <sub>D</sub> = 3 V, V <sub>S</sub> = 1 V; V <sub>D</sub> = 1 V, V <sub>S</sub> = 3 V;<br>Test Circuit 2  |
| Channel ON Leakage I <sub>D</sub> , I <sub>S</sub> (ON)  | ±0.01<br>±0.5          | ±1      | ±1.5                   | nA typ<br>nA max | V <sub>D</sub> = V <sub>S</sub> = 3 V; V <sub>D</sub> = V <sub>S</sub> = 1 V; Test Circuit 3               |
| DIGITAL INPUTS                                           |                        |         |                        |                  |                                                                                                            |
| Input High Voltage, V <sub>INH</sub>                     |                        |         | 2.0                    | V min            |                                                                                                            |
| Input Low Voltage, V <sub>INL</sub>                      |                        |         | 0.8                    | V max            |                                                                                                            |
| Input Current<br>I <sub>INL</sub> or I <sub>INH</sub>    | 0.001                  |         |                        | μA typ<br>μA max | V <sub>IN</sub> = V <sub>INL</sub> or V <sub>INH</sub>                                                     |
|                                                          |                        |         | ±0.5                   |                  |                                                                                                            |
| DYNAMIC CHARACTERISTICS <sup>2</sup>                     |                        |         |                        |                  |                                                                                                            |
| t <sub>ON</sub>                                          |                        | 8<br>16 | 21                     | ns typ<br>ns max | R <sub>L</sub> = 100 Ω, C <sub>L</sub> = 35 pF,<br>V <sub>S</sub> = +1.5 V; Test Circuit 4                 |
| t <sub>OFF</sub>                                         |                        | 5<br>10 | 11                     | ns typ<br>ns max | R <sub>L</sub> = 100 Ω, C <sub>L</sub> = 35 pF,<br>V <sub>S</sub> = +1.5 V; Test Circuit 4                 |
| Break-Before-Make Time Delay, t <sub>D</sub>             |                        | 5<br>1  |                        | ns typ<br>ns min | R <sub>L</sub> = 100 Ω, C <sub>L</sub> = 35 pF,<br>V <sub>S1</sub> = V <sub>S2</sub> = 3 V; Test Circuit 5 |
| Off Isolation                                            |                        | –65     |                        | dB typ           | R <sub>L</sub> = 50 Ω, f = 10 MHz; Test Circuit 7                                                          |
| Channel-to-Channel Crosstalk                             |                        | –75     |                        | dB typ           | R <sub>L</sub> = 50 Ω, f = 10 MHz; Test Circuit 8                                                          |
| Bandwidth –3 dB                                          |                        | 240     |                        | MHz typ          | R <sub>L</sub> = 50 Ω; Test Circuit 6                                                                      |
| Distortion                                               |                        | 2       |                        | % typ            | R <sub>L</sub> = 50 Ω                                                                                      |
| Charge Injection                                         |                        | 3       |                        | pC typ           | C <sub>L</sub> = 1 nF; Test Circuit 9                                                                      |
| C <sub>S</sub> (OFF)                                     |                        | 10      |                        | pF typ           | f = 1 kHz                                                                                                  |
| C <sub>D</sub> (OFF)                                     |                        | 20      |                        | pF typ           | f = 1 kHz                                                                                                  |
| C <sub>D</sub> , C <sub>S</sub> (ON)                     |                        | 30      |                        | pF typ           | f = 1 MHz                                                                                                  |
| POWER REQUIREMENTS                                       |                        |         |                        |                  |                                                                                                            |
| I <sub>DD</sub>                                          | 0.001                  | 1       | 1                      | μA max<br>μA typ | V <sub>DD</sub> = +3.3 V<br>Digital Inputs = 0 V or V <sub>DD</sub>                                        |
| I <sub>IN</sub>                                          |                        | 1       | 1                      | μA typ           | V <sub>IN</sub> = +3 V                                                                                     |
| I <sub>O</sub>                                           |                        | 100     |                        | mA max           | V <sub>S</sub> /V <sub>D</sub> = 0 V                                                                       |

## NOTES

<sup>1</sup>Temperature range: B Version, –40°C to +125°C.<sup>2</sup>Guaranteed by design, not subject to production test.

Specifications subject to change without notice.

Table I. Truth Table

| $\overline{\text{EN}}$ | IN | D1   | D2   | D3   | D4   | Function |
|------------------------|----|------|------|------|------|----------|
| 1                      | X  | Hi-Z | Hi-Z | Hi-Z | Hi-Z | DISABLE  |
| 0                      | 0  | S1A  | S2A  | S3A  | S4A  | IN = 0   |
| 0                      | 1  | S1B  | S2B  | S3B  | S4B  | IN = 1   |

# ADG774

## ABSOLUTE MAXIMUM RATINGS<sup>1</sup>

(T<sub>A</sub> = 25°C unless otherwise noted.)

|                                     |                                                                       |
|-------------------------------------|-----------------------------------------------------------------------|
| V <sub>DD</sub> to GND              | –0.3 V to +6 V                                                        |
| Analog, Digital Inputs <sup>2</sup> | –0.3 V to V <sub>DD</sub> + 0.3 V or<br>30 mA, Whichever Occurs First |
| Continuous Current, S or D          | 100 mA                                                                |
| Peak Current, S or D                | 300 mA<br>(Pulsed at 1 ms, 10% Duty Cycle max)                        |
| Operating Temperature Range         |                                                                       |
| Industrial (B Version)              | –40°C to +125°C                                                       |
| Storage Temperature Range           | –65°C to +150°C                                                       |
| Junction Temperature                | 150°C                                                                 |
| SOIC Package, Power Dissipation     | 600 mW                                                                |
| θ <sub>JA</sub> Thermal Impedance   | 100°C/W                                                               |

|                                        |            |
|----------------------------------------|------------|
| QSOP Package, Power Dissipation        | 566 mW     |
| θ <sub>JA</sub> Thermal Impedance      | 149.97°C/W |
| Lead Temperature, Soldering (10 sec)   | 300°C      |
| I R Reflow, Peak Temperature (<20 sec) | 235°C      |
| ESD                                    | 2 kV       |

## NOTES

<sup>1</sup>Stresses above those listed under Absolute Maximum Ratings may cause permanent damage to the device. This is a stress rating only; functional operation of the device at these or any other conditions above those listed in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability. Only one absolute maximum rating may be applied at any one time.

<sup>2</sup>Overvoltages at IN, S, or D will be clamped by internal diodes. Current should be limited to the maximum ratings given.

## ORDERING GUIDE

| Model             | Temperature Range | Package Descriptions                  | Package Options |
|-------------------|-------------------|---------------------------------------|-----------------|
| ADG774BR          | –40°C to +125°C   | Standard Small Outline Package (SOIC) | R-16            |
| ADG774BR-REEL     | –40°C to +125°C   | Standard Small Outline Package (SOIC) | R-16            |
| ADG774BR-REEL7    | –40°C to +125°C   | Standard Small Outline Package (SOIC) | R-16            |
| ADG774BRZ*        | –40°C to +125°C   | Standard Small Outline Package (SOIC) | R-16            |
| ADG774BRZ-REEL*   | –40°C to +125°C   | Standard Small Outline Package (SOIC) | R-16            |
| ADG774BRZ-REEL7*  | –40°C to +125°C   | Standard Small Outline Package (SOIC) | R-16            |
| ADG774BRQ         | –40°C to +125°C   | Shrink Small Outline Package (QSOP)   | RQ-16           |
| ADG774BRQ-REEL    | –40°C to +125°C   | Shrink Small Outline Package (QSOP)   | RQ-16           |
| ADG774BRQ-REEL7   | –40°C to +125°C   | Shrink Small Outline Package (QSOP)   | RQ-16           |
| ADG774BRQZ*       | –40°C to +125°C   | Shrink Small Outline Package (QSOP)   | RQ-16           |
| ADG774BRQZ-REEL*  | –40°C to +125°C   | Shrink Small Outline Package (QSOP)   | RQ-16           |
| ADG774BRQZ-REEL7* | –40°C to +125°C   | Shrink Small Outline Package (QSOP)   | RQ-16           |

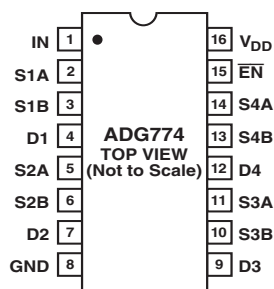
\*Z = Pb-free part.

## CAUTION

ESD (electrostatic discharge) sensitive device. Electrostatic charges as high as 4000 V readily accumulate on the human body and test equipment and can discharge without detection. Although the ADG774 features proprietary ESD protection circuitry, permanent damage may occur on devices subjected to high energy electrostatic discharges. Therefore, proper ESD precautions are recommended to avoid performance degradation or loss of functionality.



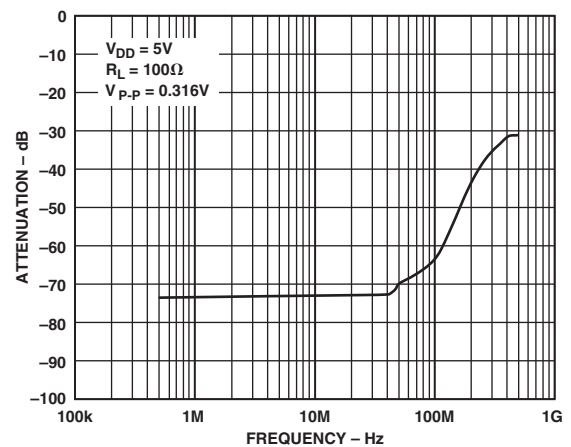
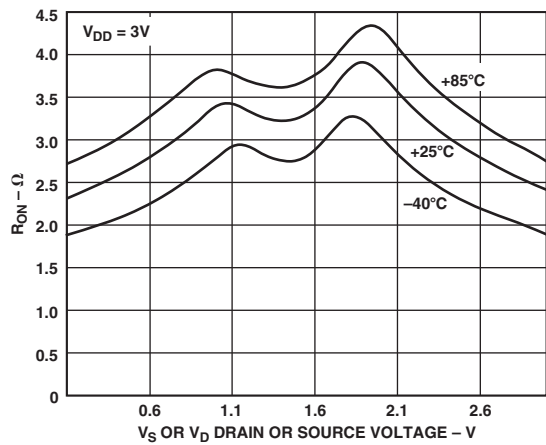
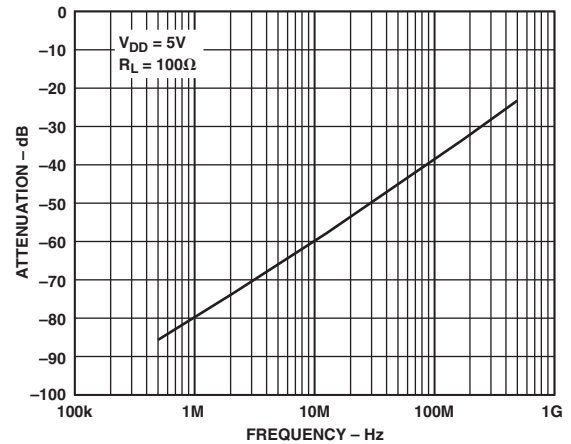
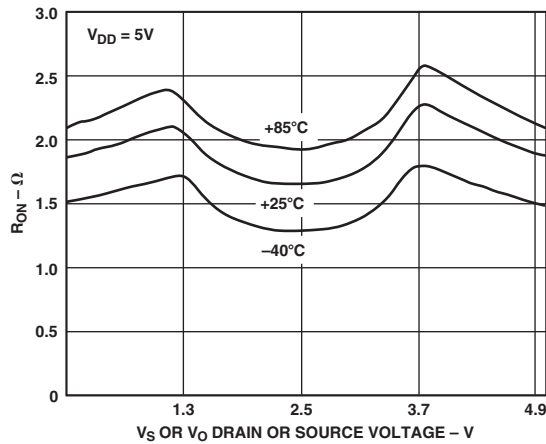
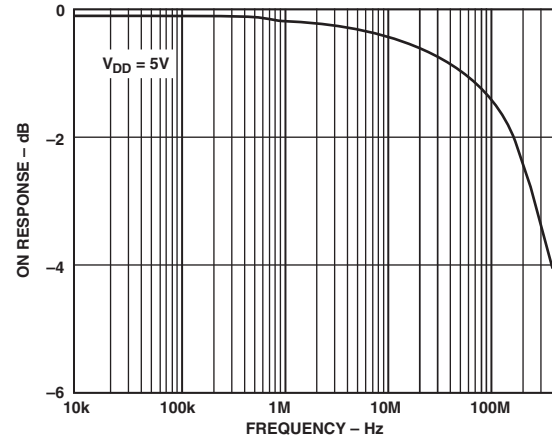
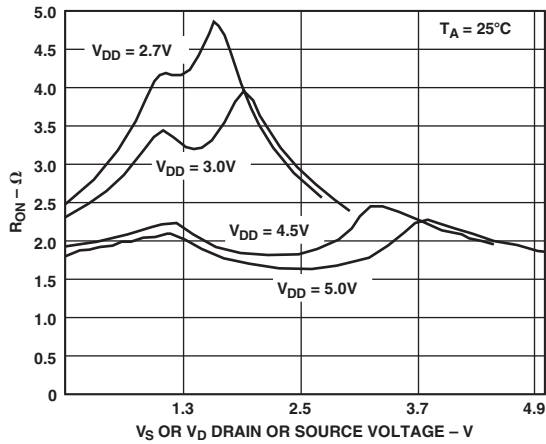
## PIN CONFIGURATION (SOIC/QSOP)

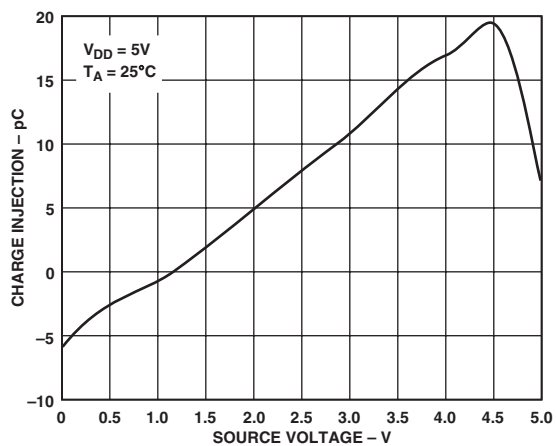


## TERMINOLOGY

|                 |                                                                                                                                                  |
|-----------------|--------------------------------------------------------------------------------------------------------------------------------------------------|
| $V_{DD}$        | Most Positive Power Supply Potential.                                                                                                            |
| GND             | Ground (0 V) Reference.                                                                                                                          |
| S               | Source Terminal. May be an input or output.                                                                                                      |
| D               | Drain Terminal. May be an input or output.                                                                                                       |
| IN              | Logic Control Input.                                                                                                                             |
| $\overline{EN}$ | Logic Control Input.                                                                                                                             |
| $R_{ON}$        | Ohmic Resistance between D and S.                                                                                                                |
| $\Delta R_{ON}$ | On Resistance Match between any Two Channels, i.e., $R_{ON\ max} - R_{ON\ min}$ .                                                                |
| $R_{FLAT(ON)}$  | Flatness is defined as the difference between the maximum and minimum value of on resistance as measured over the specified analog signal range. |
| $I_S$ (OFF)     | Source Leakage Current with the Switch OFF.                                                                                                      |
| $I_D$ (OFF)     | Drain Leakage Current with the Switch OFF.                                                                                                       |
| $I_D, I_S$ (ON) | Channel Leakage Current with the Switch ON.                                                                                                      |
| $V_D$ ( $V_S$ ) | Analog Voltage on Terminals D, S.                                                                                                                |
| $C_S$ (OFF)     | OFF Switch Source Capacitance.                                                                                                                   |
| $C_D$ (OFF)     | OFF Switch Drain Capacitance.                                                                                                                    |
| $C_D, C_S$ (ON) | ON Switch Capacitance.                                                                                                                           |
| $t_{ON}$        | Delay between Applying the Digital Control Input and the Output Switching on. See Test Circuit 4.                                                |
| $t_{OFF}$       | Delay between Applying the Digital Control Input and the Output Switching Off.                                                                   |
| $t_D$           | OFF Time or ON Time Measured between the 90% Points of Both Switches, When Switching from One Address State to Another. See Test Circuit 5.      |
| Crosstalk       | A Measure of Unwanted Signal that is Coupled through from One Channel to Another as a Result of Parasitic Capacitance.                           |
| Off Isolation   | A Measure of Unwanted Signal Coupling through an OFF Switch.                                                                                     |
| Bandwidth       | Frequency Response of the Switch in the ON State Measured at 3 dB Down.                                                                          |
| Distortion      | $R_{FLAT(ON)}/R_L$                                                                                                                               |

# ADG774—Typical Performance Characteristics





TPC 7. Charge Injection vs. Source Voltage

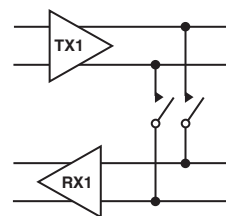


Figure 1. Loop Back

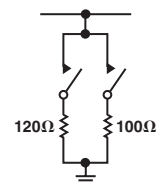


Figure 2. Line Termination

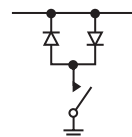
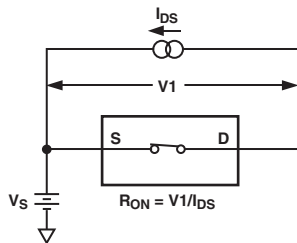


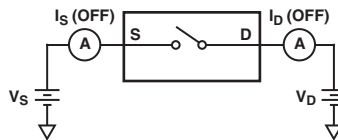
Figure 3. Line Clamp

# ADG774

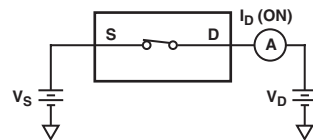
## Test Circuits



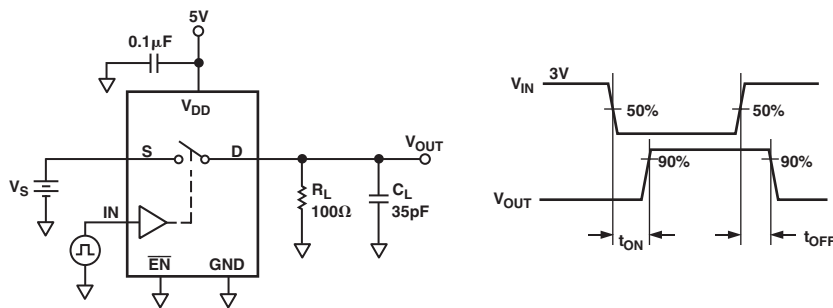
Test Circuit 1. On Resistance



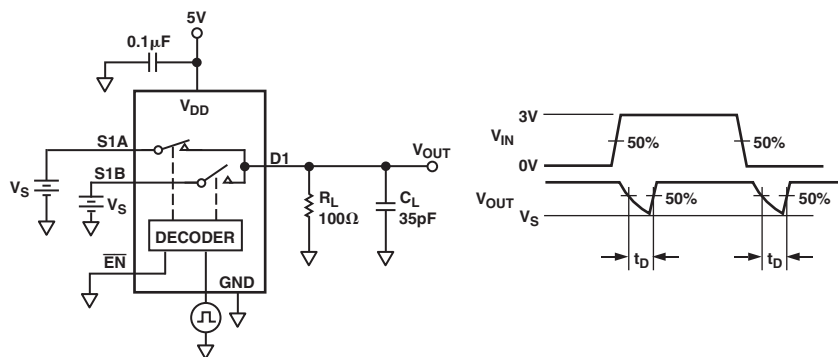
Test Circuit 2. Off Leakage



Test Circuit 3. On Leakage

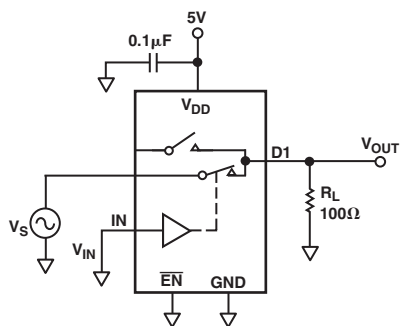


Test Circuit 4. Switching Times

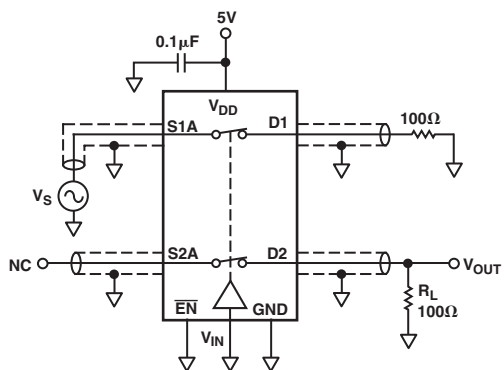


Test Circuit 5. Break-Before-Make Time Delay



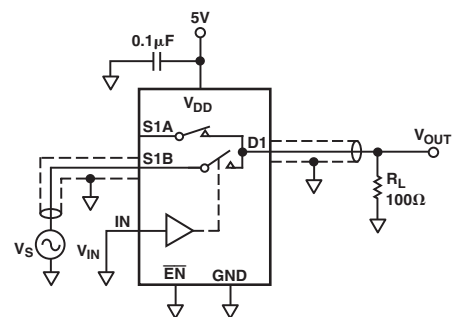


Test Circuit 6. Bandwidth

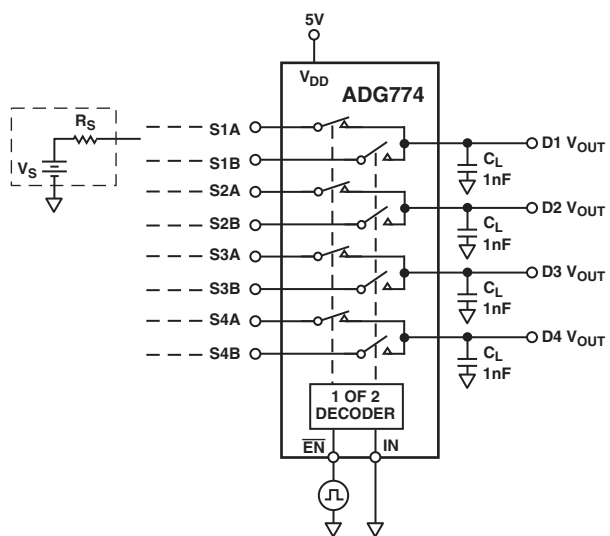


$$\text{CHANNEL-TO-CHANNEL CROSSTALK} = 20 \times \log |V_S/V_{OUT}|$$

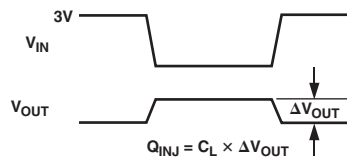
Test Circuit 7. Channel-to-Channel Crosstalk



Test Circuit 8. Off Isolation



Test Circuit 9. Charge Injection

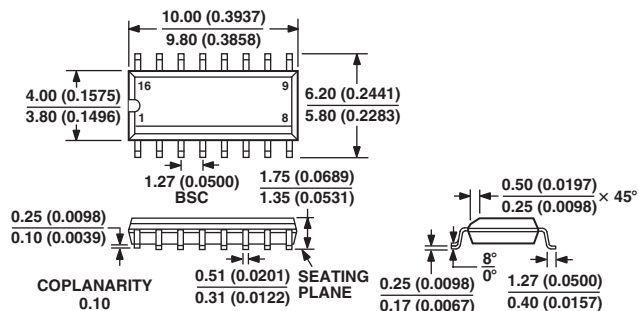


$$Q_{INJ} = C_L \times \Delta V_{OUT}$$

## OUTLINE DIMENSIONS

**16-Lead Standard Small Outline Package [SOIC]  
Narrow Body  
(R-16)**

Dimensions shown in millimeters and (inches)

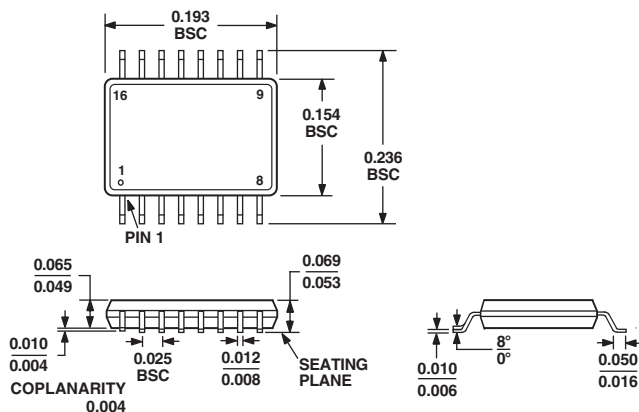


COMPLIANT TO JEDEC STANDARDS MS-012AC

CONTROLLING DIMENSIONS ARE IN MILLIMETERS; INCH DIMENSIONS (IN PARENTHESES) ARE ROUNDED-OFF MILLIMETER EQUIVALENTS FOR REFERENCE ONLY AND ARE NOT APPROPRIATE FOR USE IN DESIGN

### 16-Lead Shrink Small Outline Package [QSOP] (RQ-16)

Dimensions shown in inches



**COMPLIANT TO JEDEC STANDARDS MO-137AB**

## Revision History

| Location                                               | Page      |
|--------------------------------------------------------|-----------|
| <b>3/04—Data Sheet changed from REV. B to REV. C.</b>  |           |
| Added APPLICATIONS .....                               | 1         |
| Changes to ORDERING GUIDE .....                        | 4         |
| <b>10/03—Data Sheet changed from REV. A to REV. B.</b> |           |
| Updated formatting .....                               | Universal |
| Renumbered TPCs and Figures .....                      | Universal |
| Changes to FEATURES .....                              | 1         |
| Changes to APPLICATIONS .....                          | 1         |
| Changes to PRODUCT HIGHLIGHTS .....                    | 1         |
| Changes to SPECIFICATIONS .....                        | 2         |
| Changes to ABSOLUTE MAXIMUM RATINGS .....              | 4         |
| Updated ORDERING GUIDE .....                           | 4         |
| Delete Figure 2 .....                                  | 7         |
| Updated OUTLINE DIMENSIONS .....                       | 10        |
| <b>4/03—Data Sheet changed from REV. 0 to REV. A.</b>  |           |
| Renumbered TPCs and Figures .....                      | Universal |
| Updated OUTLINE DIMENSIONS .....                       | 8         |



Компания «Life Electronics» занимается поставками электронных компонентов импортного и отечественного производства от производителей и со складов крупных дистрибьюторов Европы, Америки и Азии.

С конца 2013 года компания активно расширяет линейку поставок компонентов по направлению коаксиальный кабель, кварцевые генераторы и конденсаторы (керамические, пленочные, электролитические), за счёт заключения дистрибьюторских договоров

Мы предлагаем:

- Конкурентоспособные цены и скидки постоянным клиентам.
- Специальные условия для постоянных клиентов.
- Подбор аналогов.
- Поставку компонентов в любых объемах, удовлетворяющих вашим потребностям.
- Приемлемые сроки поставки, возможна ускоренная поставка.
- Доставку товара в любую точку России и стран СНГ.
- Комплексную поставку.
- Работу по проектам и поставку образцов.
- Формирование склада под заказчика.
- Сертификаты соответствия на поставляемую продукцию (по желанию клиента).
- Тестирование поставляемой продукции.
- Поставку компонентов, требующих военную и космическую приемку.
- Входной контроль качества.
- Наличие сертификата ISO.

В составе нашей компании организован Конструкторский отдел, призванный помогать разработчикам, и инженерам.

Конструкторский отдел помогает осуществить:

- Регистрацию проекта у производителя компонентов.
- Техническую поддержку проекта.
- Защиту от снятия компонента с производства.
- Оценку стоимости проекта по компонентам.
- Изготовление тестовой платы монтаж и пусконаладочные работы.



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